

Absolute Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	40	V
Collector-Emitter Voltage	V _{CEO}	40	V
Emitter-Base Voltage	V _{EBO}	6	V
Collector Current - Continuous	I _C	500	mA
Peak Pulse Collector Current	I _{CM}	1	A
Peak Base Current	I _{BM}	100	mA

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

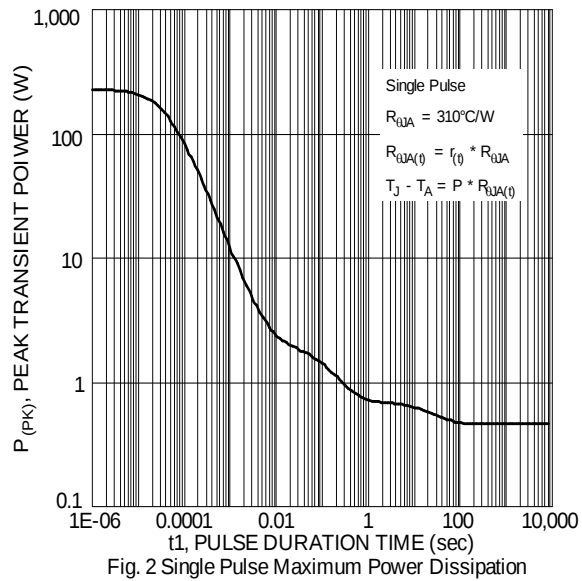
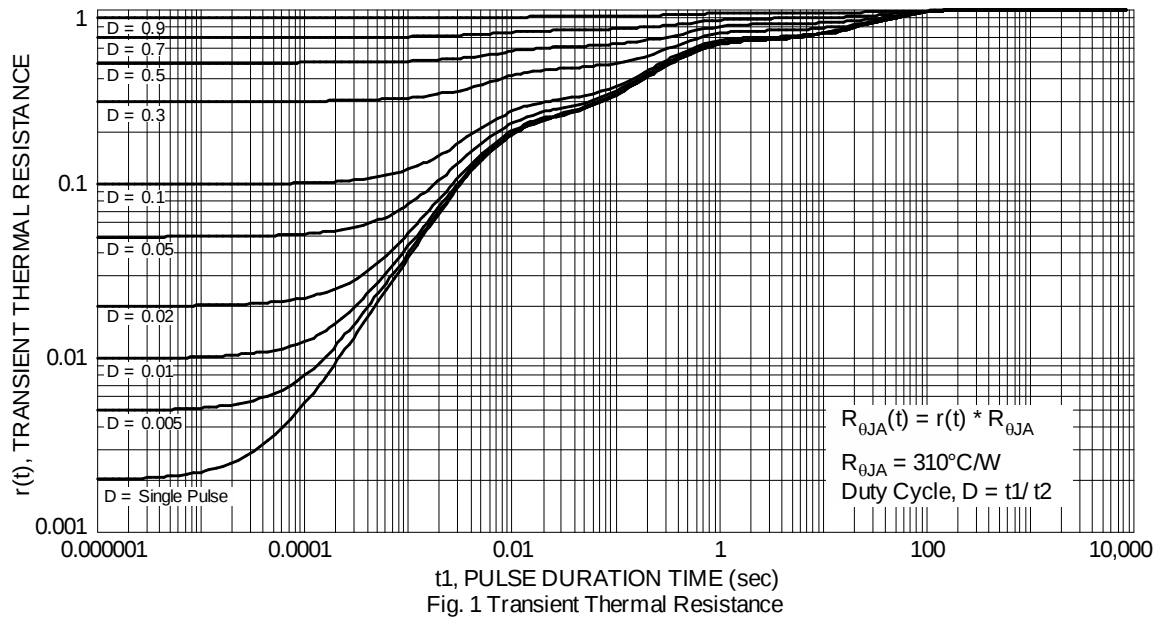
Characteristic	Symbol	Value	Unit
Power Dissipation	P _D	400	mW
		1000	
Thermal Resistance, Junction to Ambient	R _{θJA}	310	°C/W
		120	
Thermal Resistance, Junction to Lead	R _{θJL}	120	°C/W
Operating and Storage and Temperature Range	T _J , T _{STG}	-55 to +150	°C

ESD Ratings (Note 8)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	B

- Notes:
5. For the device mounted on minimum recommended pad layout 1oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in steady state condition. The entire exposed collector pad is attached to the heatsink.
 6. Same as Note 5, except the exposed collector pad is mounted on 25mm x 25mm 2oz copper.
 7. Thermal resistance from junction to solder-point (on the exposed collector pad).
 8. Refer to JEDEC specification JESD22-A114 and JESD22-A115.

Thermal Characteristics



Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS						
Collector-Base Breakdown Voltage	BV _{CBO}	40	—	—	V	I _C = 100μA, I _E = 0
Collector-Emitter Breakdown Voltage (Note 9)	BV _{CEO}	40	—	—	V	I _C = 10mA, I _B = 0
Emitter-Base Breakdown Voltage	BV _{EBO}	6	—	—	V	I _E = 100μA, I _C = 0
Collector Cutoff Current	I _{CBO}	—	—	100 50	nA μA	V _{CB} = 30V, I _E = 0 V _{CB} = 30V, I _E = 0, T _A = +150°C
Emitter Cutoff Current	I _{EBO}	—	—	100	nA	V _{EB} = 5V, I _C = 0
ON CHARACTERISTICS (Note 9)						
DC Current Gain	h _{FE}	200 150 50	— — —	— — —	—	V _{CE} = 2V, I _C = 10mA V _{CE} = 2V, I _C = 100mA V _{CE} = 2V, I _C = 500mA
Collector-Emitter Saturation Voltage	V _{CE(sat)}	— — — —	— — — —	50 100 200 250	mV	I _C = 10mA, I _B = 0.5mA I _C = 100mA, I _B = 5mA I _C = 200mA, I _B = 10mA I _C = 500mA, I _B = 50mA
Collector-Emitter Saturation Resistance	R _{CE(sat)}	—	—	500	mΩ	I _C = 500mA, I _B = 50mA
Base-Emitter Saturation Voltage	V _{BE(sat)}	—	—	1.2	V	I _C = 500mA, I _B = 50mA
Base-Emitter Turn On Voltage	V _{BE(on)}	—	—	1.1	V	V _{CE} = 2V, I _C = 100mA
SMALL SIGNAL CHARACTERISTICS						
Output Capacitance	C _{obo}	—	—	6	pF	V _{CB} = 10V, f = 1.0MHz
Current Gain-Bandwidth Product	f _T	250	300	—	MHz	V _{CE} = 5V, I _C = 100mA, f = 100MHz

Note: 9. Measured under pulsed conditions. Pulse width ≤ 300μs. Duty cycle ≤ 2%.

Typical Electrical Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

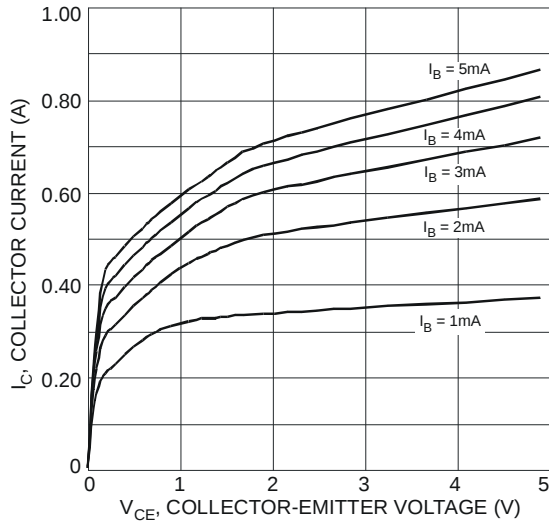


Fig. 4 Typical Collector Current vs. Collector-Emitter Voltage

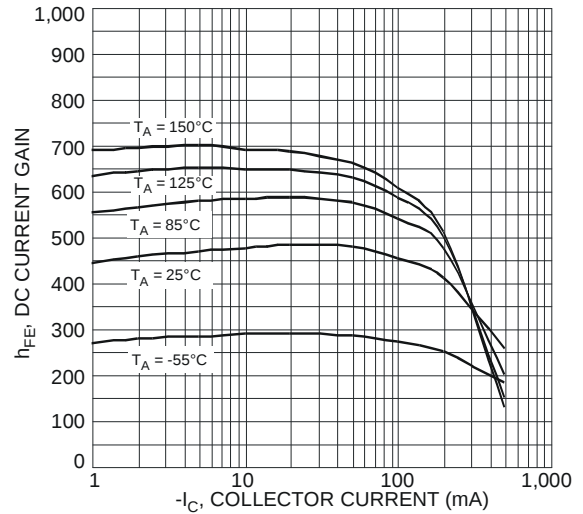


Fig. 5 Typical DC Current Gain vs. Collector Current

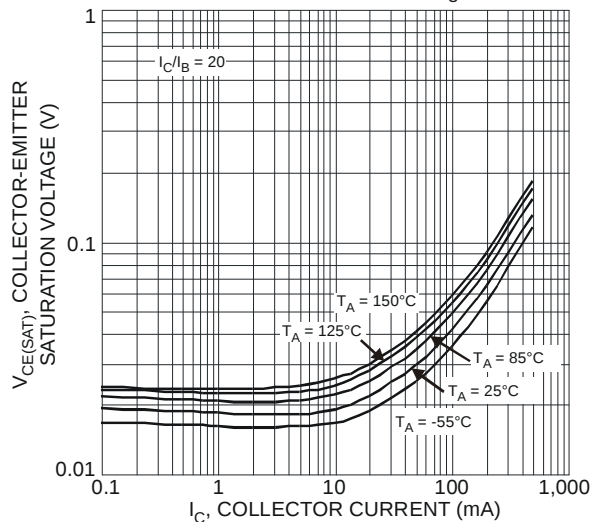


Fig. 6 Typical Collector-Emitter Saturation Voltage vs. Collector Current

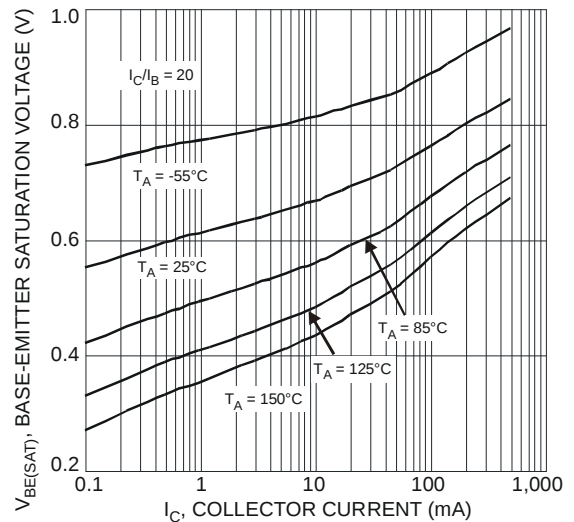


Fig. 7 Typical Base-Emitter Saturation Voltage vs. Collector Current

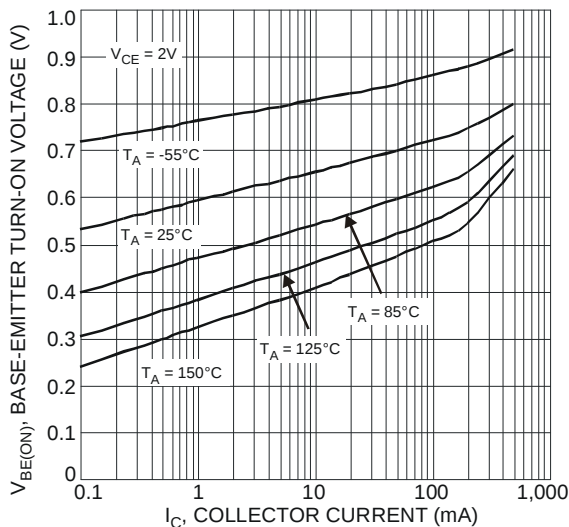


Fig. 8 Typical Base-Emitter Turn-On Voltage vs. Collector Current

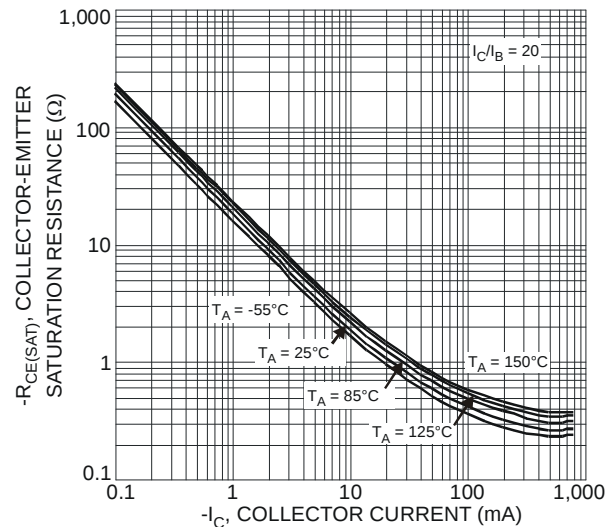
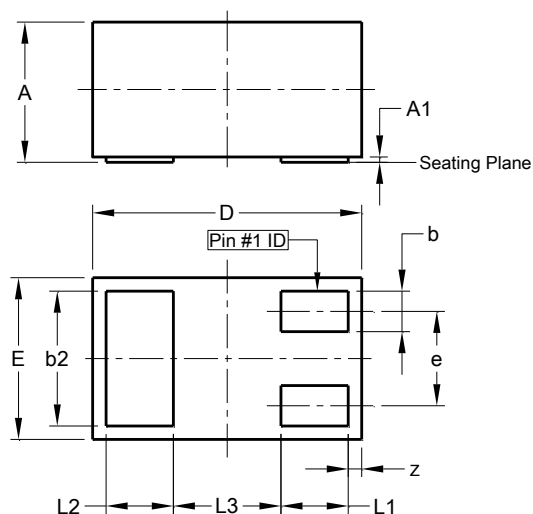


Fig. 9 Typical Collector-Emitter Saturation Resistance vs. Collector Current

Package Outline Dimensions

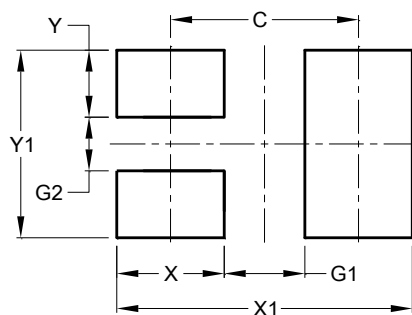
Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for the latest version.



X1-DFN1006-3			
Dim	Min	Max	Typ
A	0.47	0.53	0.50
A1	0.00	0.05	0.03
b	0.10	0.20	0.15
b2	0.45	0.55	0.50
D	0.95	1.075	1.00
E	0.55	0.675	0.60
e	-	-	0.35
L1	0.20	0.30	0.25
L2	0.20	0.30	0.25
L3	-	-	0.40
z	0.02	0.08	0.05
All Dimensions in mm			

Suggested Pad Layout

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.



Dimensions	Value (in mm)
C	0.70
G1	0.30
G2	0.20
X	0.40
X1	1.10
Y	0.25
Y1	0.70

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